

# Tao Zhang

## List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	A 5.8-GHz High-Power and High-Efficiency Rectifier Circuit With Lateral GaN Schottky Diode for Wireless Power Transfer. IEEE Transactions on Power Electronics, 2020, 35, 2247-2252.	7.9	60
2	A $3\text{ kV}/2.94\text{ m}\Omega\text{ cm}^2$ and Low Leakage Current With Low Turn-On Voltage Lateral GaN Schottky Barrier Diode on Silicon Substrate With Anode Engineering Technique. IEEE Electron Device Letters, 2019, 40, 1583-1586.	3.9	50
3	Lateral GaN Schottky Barrier Diode for Wireless High-Power Transfer Application With High RF/DC Conversion Efficiency: From Circuit Construction and Device Technologies to System Demonstration. IEEE Transactions on Industrial Electronics, 2020, 67, 6597-6606.	7.9	32
4	Trap state analysis in AlGaIn/GaN/AlGaIn double heterostructure high electron mobility transistors at high temperatures. Applied Physics Letters, 2017, 110, 252102.	3.3	27
5	High-performance lateral GaN Schottky barrier diode on silicon substrate with low turn-on voltage of 0.31 V, high breakdown voltage of 2.65 kV and high-power figure-of-merit of $2.65\text{ GW cm}^2$ . Applied Physics Express, 2019, 12, 046502.	2.4	27
6	A $1.9\text{ kV}/2.61\text{ m}\Omega\text{ cm}^2$ Lateral GaN Schottky Barrier Diode on Silicon Substrate with Tungsten Anode and Low Turn-On Voltage of 0.35 V. IEEE Electron Device Letters, 2018, , 1-1.	3.9	23
7	AlGaIn-Channel Gate Injection Transistor on Silicon Substrate With Adjustable $4\text{--}7\text{ V}$ Threshold Voltage and $1.3\text{-kV}$ Breakdown Voltage. IEEE Electron Device Letters, 2018, 39, 1026-1029.	3.9	21
8	Current-Collapse Suppression of High-Performance Lateral AlGaIn/GaN Schottky Barrier Diodes by a Thick GaN Cap Layer. IEEE Electron Device Letters, 2021, 42, 477-480.	3.9	18
9	High-Performance E-Mode $\text{p}$ -Channel GaN FinFET on Silicon Substrate With High $\text{I}_{\text{ON}}/\text{I}_{\text{OFF}}$ and High Threshold Voltage. IEEE Electron Device Letters, 2022, 43, 705-708.	3.9	16
10	Leakage current mechanisms of groove-type tungsten-anode GaN SBDs with ultra low turn-ON voltage and low reverse current. Solid-State Electronics, 2020, 169, 107807.	1.4	15
11	Comprehensive Annealing Effects on AlGaIn/GaN Schottky Barrier Diodes With Different Work-Function Metals. IEEE Transactions on Electron Devices, 2021, 68, 2661-2666.	3.0	15
12	InGaIn-channel high-electron-mobility transistor with enhanced linearity and high-temperature performance. Applied Physics Express, 2018, 11, 094101.	2.4	13
13	Current Transport Mechanism of High-Performance Novel GaN MIS Diode. IEEE Electron Device Letters, 2021, 42, 304-307.	3.9	12
14	Investigation on the interface trap characteristics in a $\text{p}$ -channel GaN MOSFET through temperature-dependent subthreshold slope analysis. Journal Physics D: Applied Physics, 2022, 55, 095112.	2.8	9
15	Mechanism of low Ohmic contact resistance to $\text{p}$ -type GaN by suppressed edge dislocations. Applied Physics Letters, 2022, 120, .	3.3	8
16	GaN High-Electron-Mobility-Transistor on Free- Standing GaN Substrate With Low Contact Resistance and State-of-the-Art $\text{I}_{\text{ON}}/\text{I}_{\text{OFF}}$ Value. IEEE Transactions on Electron Devices, 2022, 69, 968-972.	3.0	7
17	Investigation of an AlGaIn-channel Schottky barrier diode on a silicon substrate with a molybdenum anode. Semiconductor Science and Technology, 2021, 36, 044003.	2.0	4
18	A $0.43\text{ V}/90\text{ nA}/\text{mm}$ Lateral AlGaIn/GaN Schottky Barrier Diode With Plasma-Free Groove Anode Technique. IEEE Electron Device Letters, 2021, 42, 1747-1750.	3.9	4

#	ARTICLE	IF	CITATIONS
19	Current transport mechanism of AlGaIn-channel Schottky barrier diode with extremely low leakage current and high blocking voltage of 2.55 kV. Applied Physics Letters, 2022, 120, 092102.	3.3	1
20	Mechanism of current-collapse free for lateral GaN Schottky barrier diodes utilizing polarization-induced hole injection. Applied Physics Letters, 2022, 120, 232101.	3.3	1